

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
- 30	0.150 at $V_{GS} = - 10$ V	- 2.2
	0.260 at $V_{GS} = - 4.5$ V	- 1.6

FEATURES

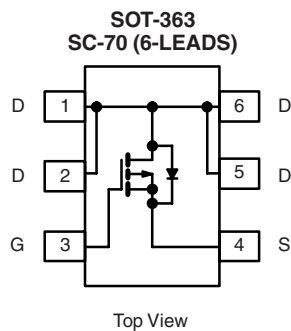
- TrenchFET[®] Power MOSFETS: 1.8 V Rated
- Thermally Enhanced SC-70 Package



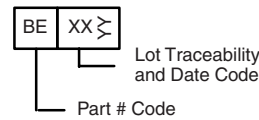
RoHS*
COMPLIANT

APPLICATIONS

- Load Switches
 - Notebook PC
 - Servers



Marking Code



Ordering Information: Si1433DH-T1
Si1433DH-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}	- 30		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	- 2.2	- 1.9	A
		$T_A = 85$ °C	- 1.7	- 1.4	
Pulsed Drain Current	I_{DM}	- 8			
Continuous Diode Current (Diode Conduction) ^a	I_S	- 1.4	- 0.9		
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	1.45	0.95	W
		$T_A = 85$ °C	0.75	0.5	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 5$ s	65	85	°C/W
		Steady State	105	130	
Maximum Junction-to-Foot (Drain)	R_{thJF}	38	48		

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.



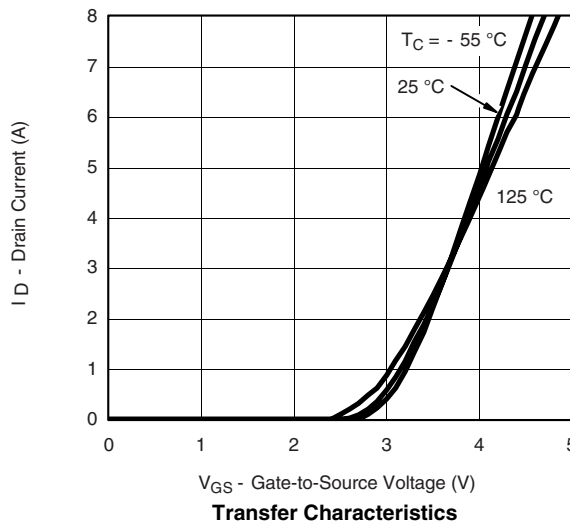
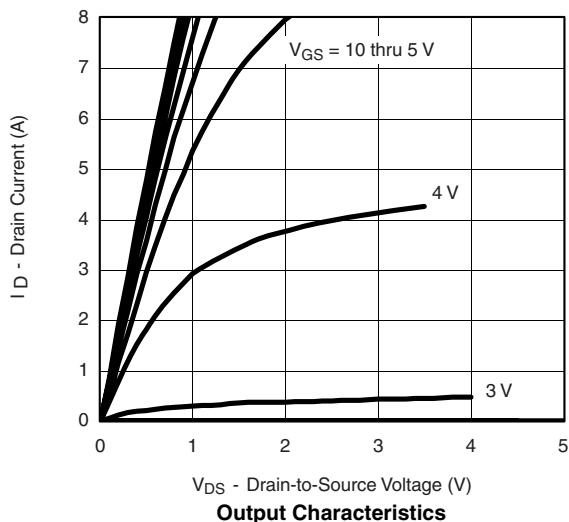
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -100\text{ }\mu\text{A}$	-1		-3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	-4			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -2.2\text{ A}$		0.120	0.150	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -1.6\text{ A}$		0.210	0.260	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -2.2\text{ A}$		4		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.2\text{ A}, V_{GS} = 0\text{ V}$		-0.85	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -2.2\text{ A}$		3.1	5	nC
Gate-Source Charge	Q_{gs}			1.0		
Gate-Drain Charge	Q_{gd}			1.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_G = 6\text{ }\Omega$		11	17	ns
Rise Time	t_r			17	26	
Turn-Off Delay Time	$t_{d(off)}$			18	27	
Fall Time	t_f			13	20	

Notes:

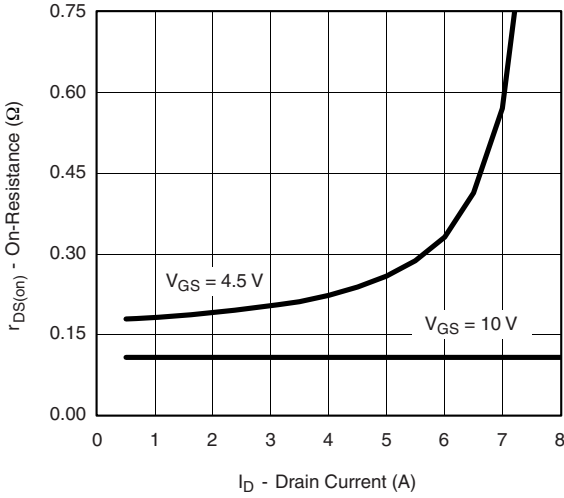
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

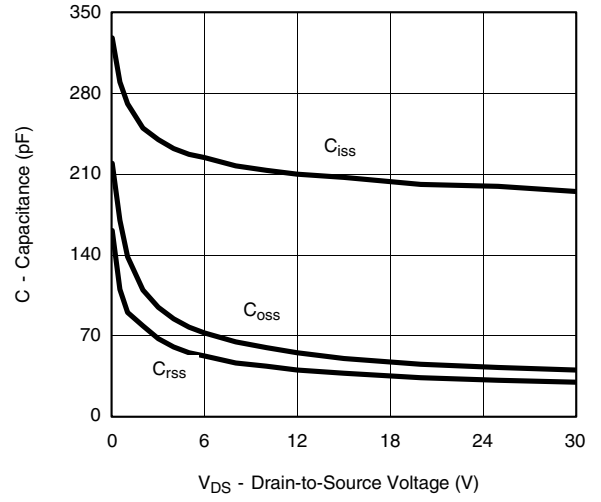
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



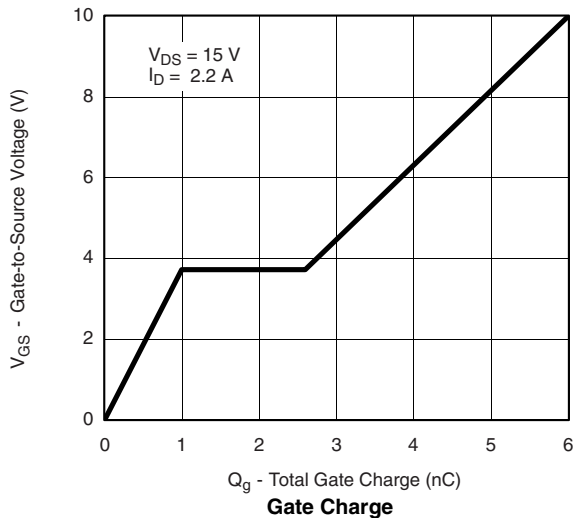
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



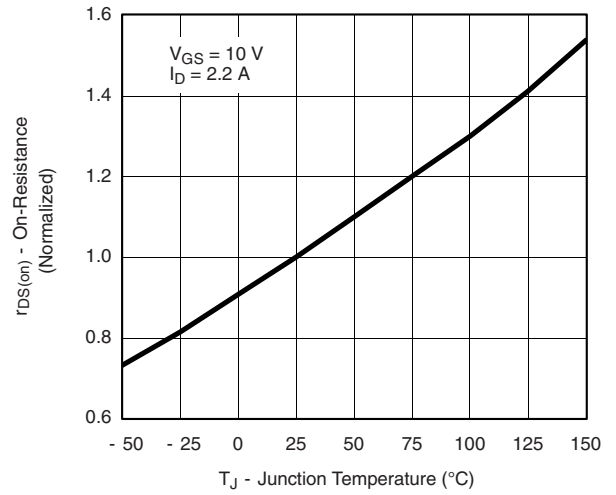
On-Resistance vs. Drain Current



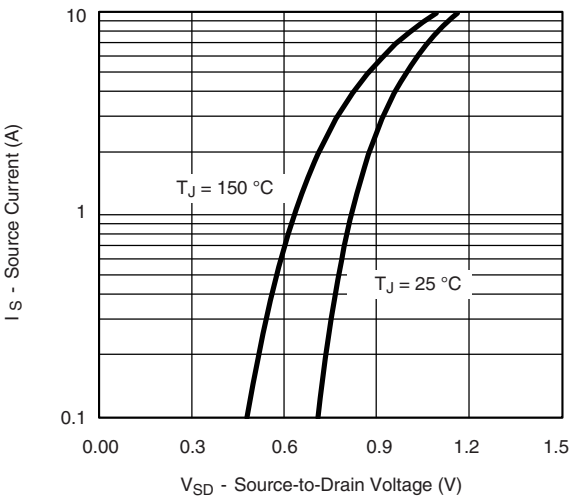
Capacitance



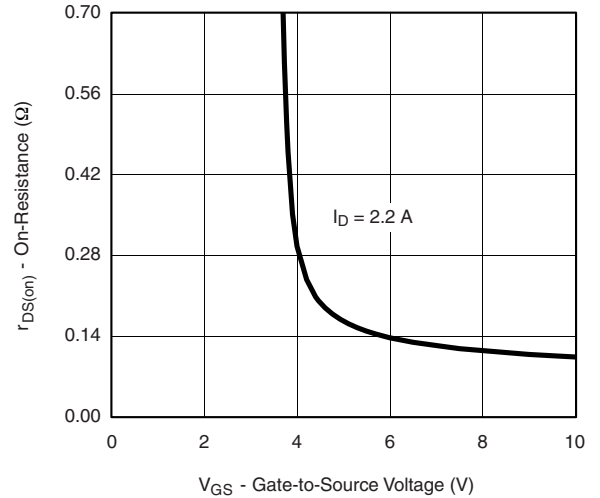
Gate Charge



On-Resistance vs. Junction Temperature



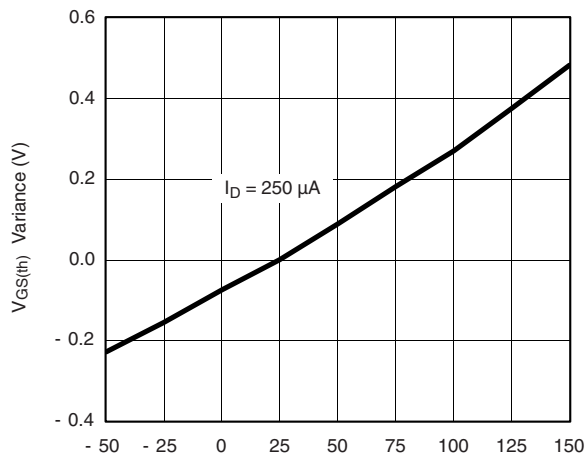
Source-Drain Diode Forward Voltage



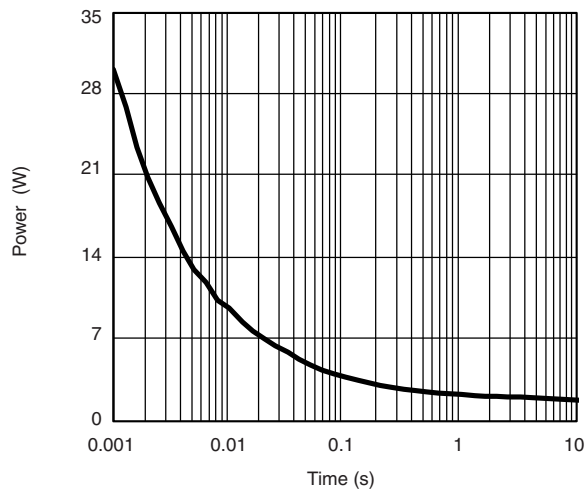
On-Resistance vs. Gate-to-Source Voltage



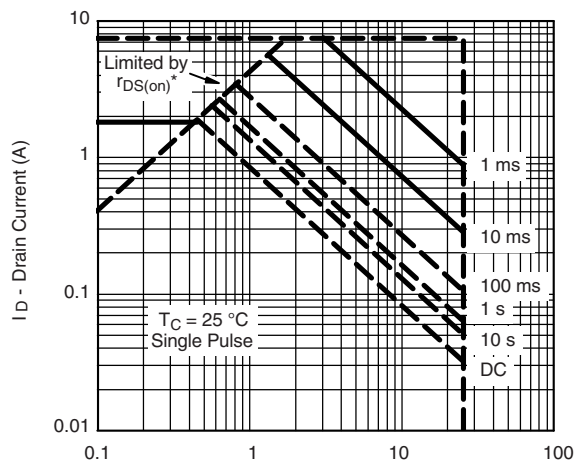
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Threshold Voltage



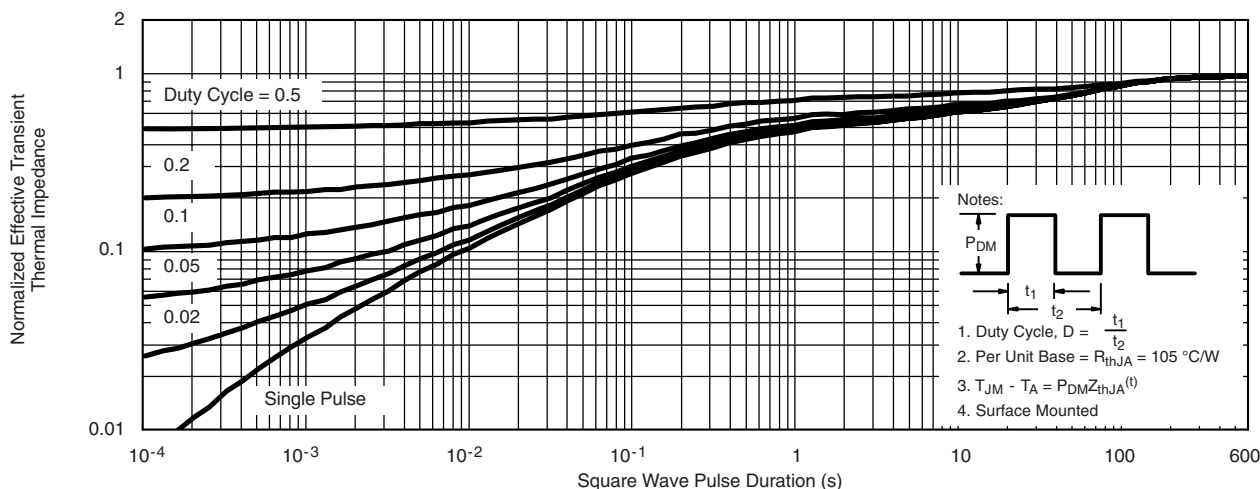
Single Pulse Power, Junction-to-Ambient



V_{DS} - Drain-to-Source Voltage (V)

* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified

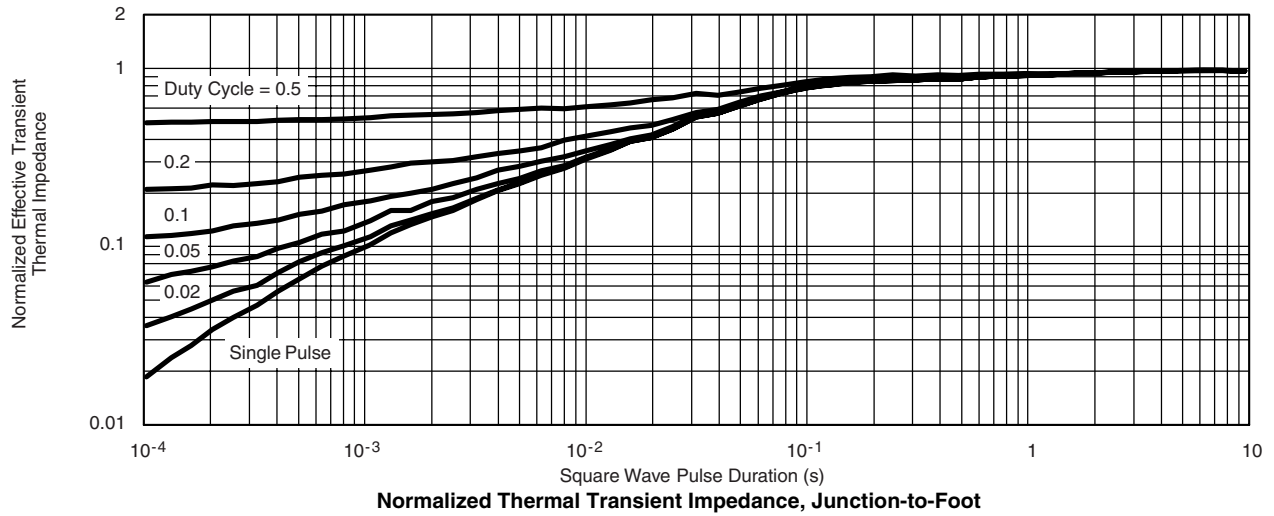
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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